Product data sheet

1. General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- · Isolated plastic package
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies
- Half-bridge lighting ballasts

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 59 °C; square-wave pulse; Fig. 1; Fig. 2	-	-	8	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_h \le 59$ °C; square-wave pulse	-	-	16	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	-	80	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	-	88	Α
Static chara	cteristics					
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.4	1.85	V
		I _F = 8 A; T _j = 25 °C	-	2	2.9	V
		I _F = 16 A; T _j = 150 °C	-	1.7	2.3	V
Dynamic ch	aracteristics			'		
t _{rr}	reverse recovery time	$I_F = 8 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 500 \text{ A/}\mu\text{s}$; $T_j = 100 \text{ °C}$	-	32	40	ns
		$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$	-	30	52	ns
		$I_F = 8 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 500 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 5	-	19	-	ns

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYC8X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

7. Marking

Table 4. Marking codes

Type number	Marking code
BYT79X-600P	BYT79X-600P

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 59 °C; square-wave pulse; Fig. 1; Fig. 2	-	8	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _h ≤ 59 °C; squarewave pulse	-	16	Α
I _{FSM}	non-repetitive peak	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse	-	80	Α
forward current	forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	88	Α
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

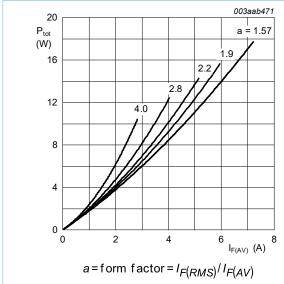


Fig. 1. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

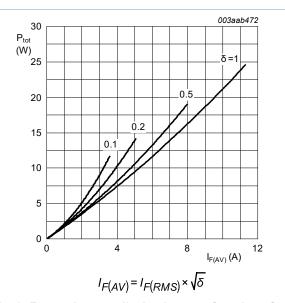


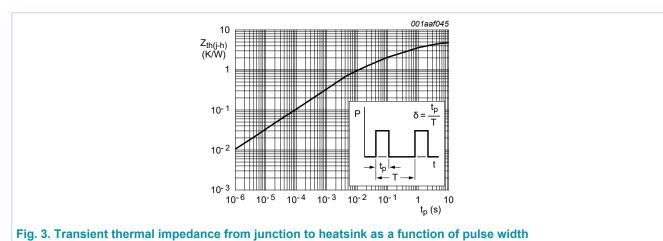
Fig. 2. Forward power dissipation as a function of average forward current; square waveform; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; Fig. 3	-	-	4.8	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air		-	55	-	K/W



10. Isolation characteristics

Table 7. Isolation characteristics

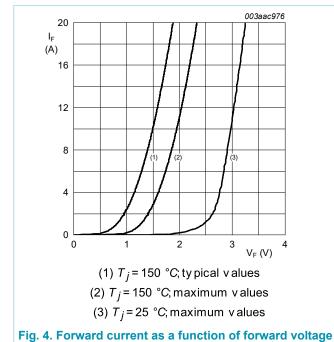
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink	-	10	-	pF

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11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V_{F}	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.4	1.85	V
		I _F = 8 A; T _j = 25 °C	-	2	2.9	V
		I _F = 16 A; T _j = 150 °C	-	1.7	2.3	V
I _R	reverse current	V _R = 500 V; T _j = 100 °C	-	1.1	3	mA
		V _R = 600 V; T _j = 25 °C	-	9	150	μΑ
Dynamic ch	naracteristics					
t _{rr}	reverse recovery time	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}$	-	32	40	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}$	-	30	52	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$	-	19	-	ns
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/$ μ s; $T_j = 100 ^{\circ}\text{C}$	-	9.5	12	А
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}$	-	1.5	5.5	А
Q _r	recovered charge	$I_F = 1 \text{ A}; V_R = 100 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}$	-	12	-	nC
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 6	-	8	10	V



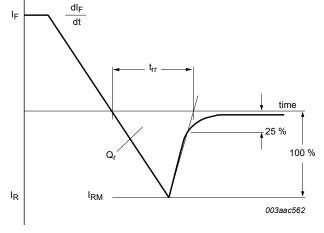
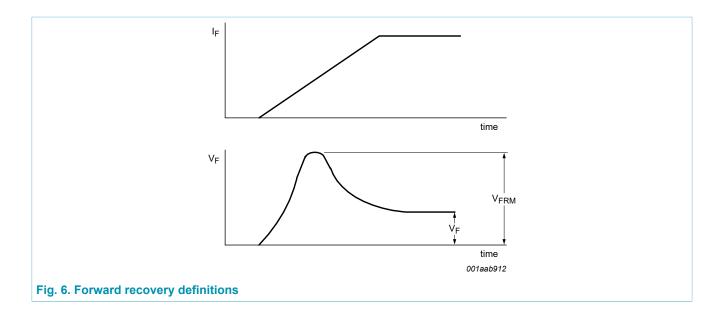


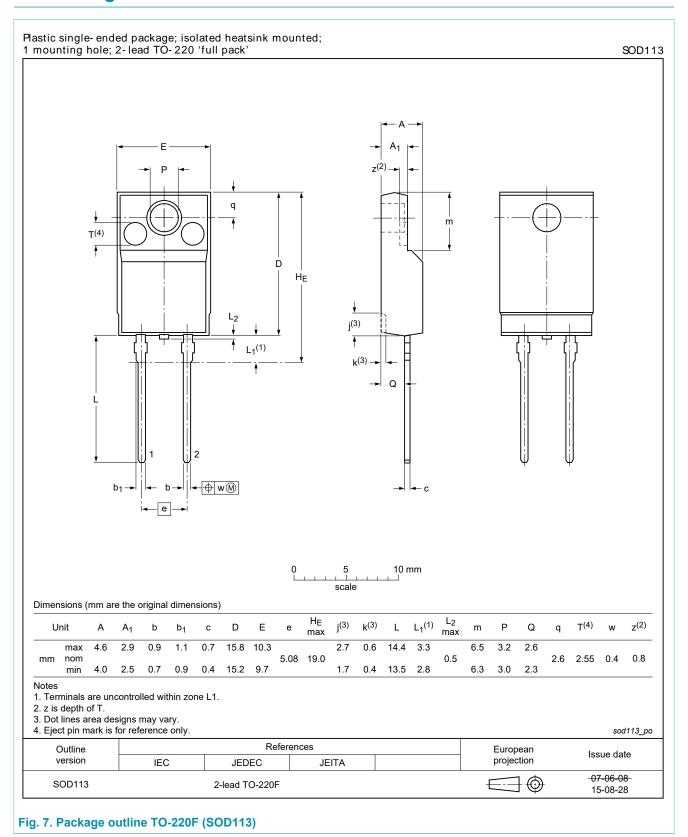
Fig. 5. Reverse recovery definitions; ramp recovery

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12. Package outline



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13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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